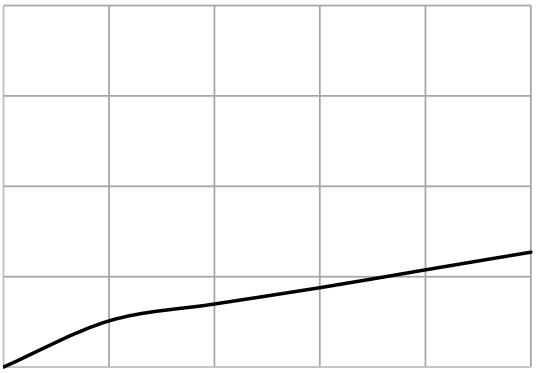
Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics					
$V_{(BR)DSS}$		40	-	-	V
I_{DSS}		-	-	1.0	μA
I_{GSS}		-	-	±100	nA
$V_{GS(th)}$		2.0	2.9	3.8	V
$R_{DS(ON)}$		-	4.6	6.0	mΩ
R_g		-	0.9	-	Ω
C_{iss}		863	1208	1631	pF
C_{oss}		538	753	1016	pF
C_{rss}		51	71	96	pF
Q_g					

Typical Performance Characteristics

Typical Performance Characteristics



Typical Performance Characteristics

Test Circuit

Figure 1: Gate Charge Test Circuit & Waveform

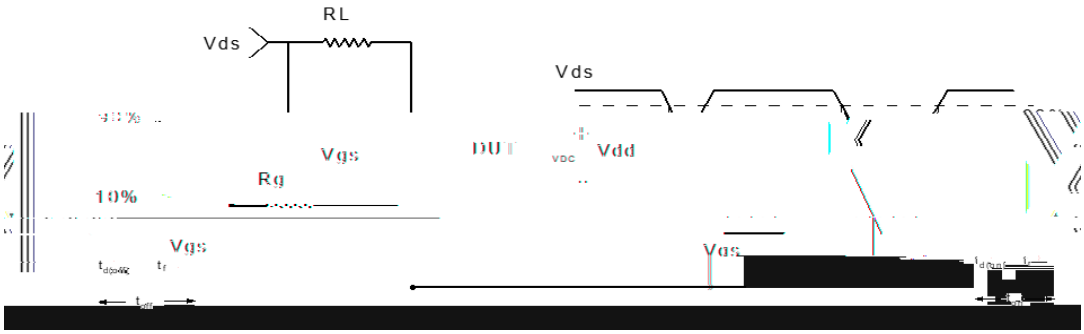


Figure 2: Resistive Switching Test Circuit & Waveform

Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

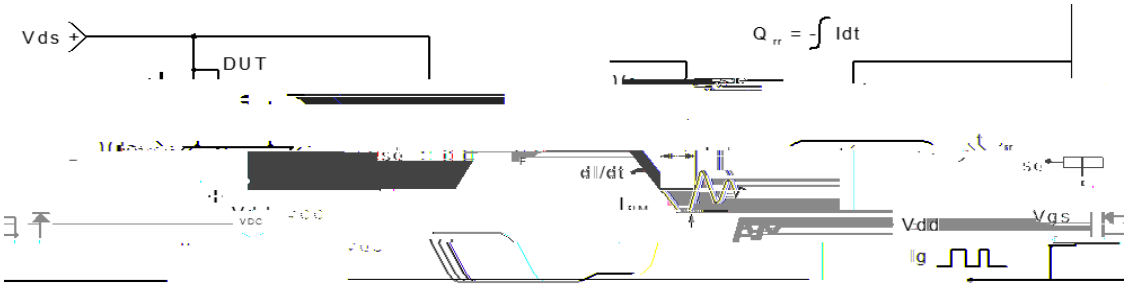


Figure 4: Diode Recovery Test Circuit & Waveform

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Package Mechanical Data(TO-252-3L)

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